

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/604,485	07/25/2003	Kun-Chih Lin	ADTP0068USA	1484
27765	7590 12/29/2004		EXAMINER	
(NAIPC) NORTH AMERICA INTERNATIONAL PATENT OFFICE			YOUNG, CHRISTOPHER G	
P.O. BOX 50 MERRIFIEL	06 .D, VA 22116		ART UNIT	PAPER NUMBER
	. _,		1756	
			DATE MAILED: 12/29/2004	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)	W				
	10/604,485	LIN, KUN-CHIH					
Office Action Summary	Examiner	Art Unit	10.00				
·	Christopher G. Young	1756					
The MAILING DATE of this communicate Period for Reply	ion appears on the cover sheet wit	h the correspondence addres	SS				
A SHORTENED STATUTORY PERIOD FOR THE MAILING DATE OF THIS COMMUNICA - Extensions of time may be available under the provisions of 37 after SIX (6) MONTHS from the mailing date of this communical If the period for reply specified above is less than thirty (30) daund If NO period for reply is specified above, the maximum statutor - Failure to reply within the set or extended period for reply will, Any reply received by the Office later than three months after the earned patent term adjustment. See 37 CFR 1.704(b).	TION. OFR 1.136(a). In no event, however, may a reation. ys, a reply within the statutory minimum of thirty period will apply and will expire SIX (6) MONT by statute, cause the application to become ABA	ply be timely filed (30) days will be considered timely. THS from the mailing date of this commu	unication.				
Status							
1) Responsive to communication(s) filed o	n <i>25 July 2003</i> .						
	☐ This action is non-final.		•				
3) Since this application is in condition for		ers, prosecution as to the me	erits is				
closed in accordance with the practice u	under <i>Ex parte Quayle</i> , 1935 C.D.	11, 453 O.G. 213.					
Disposition of Claims							
4)⊠ Claim(s) <u>1-20</u> is/are pending in the appl	ication.						
,	4a) Of the above claim(s) is/are withdrawn from consideration.						
5)⊠ Claim(s) <u>1-6,8-17,19 and 20</u> is/are allow							
6)⊠ Claim(s) 7 and 18 is/are rejected.							
7) Claim(s) is/are objected to.							
8) Claim(s) are subject to restriction	and/or election requirement.						
Application Papers							
9) The specification is objected to by the Ex	xaminer.						
10)⊠ The drawing(s) filed on <u>25 July 2003</u> is/a	<u></u>	ed to by the Examiner.					
Applicant may not request that any objection		•					
Replacement drawing sheet(s) including the	correction is required if the drawing(s	s) is objected to. See 37 CFR 1	.121(d).				
11) The oath or declaration is objected to by	the Examiner. Note the attached	Office Action or form PTO-1	152.				
Priority under 35 U.S.C. § 119		i					
 12) Acknowledgment is made of a claim for a) All b) Some * c) None of: 1. Certified copies of the priority doc 2. Certified copies of the priority doc 3. Copies of the certified copies of the application from the International 	cuments have been received. cuments have been received in Ap ne priority documents have been r	plication No	ge				
* See the attached detailed Office action for	` ' ' '	eceived.					
	,						
Attachment(s)							
1) Notice of References Cited (PTO-892)	4) T Interview St	ımmary (PTO-413)					
2) Notice of Praftsperson's Patent Drawing Review (PTO-	948) Paper No(s)	/Mail Date					
 Information Disclosure Statement(s) (PTO-1449 or PTC Paper No(s)/Mail Date 	5) Notice of Inf 6) Other:	formal Patent Application (PTO-15)	2)				

DETAILED ACTION

Claim Rejections - 35 USC § 112

1. The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

- 2. Claims 7 and 18 are rejected under 35 U.S.C. 1 12, first paragraph, because the specification, while being enabling for using an excimer laser to irradiate the amorphous film, to form a polysilicon film in the first region, does not reasonably provide enablement for the amorphous silicon film in the second region become completely melted and the amorphous silicon film in the first region become partially melted. The specification does not enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the invention commensurate in scope with these claims. The specification describes the amorphous silicon film in the first region being completely melted and the amorphous silicon film on the second region not melted or partially melted.
- 3. The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

4. Claims 7 and 18 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Each of these claims refers to the laser incorrectly in line 1. The claims call for a "layer", but the term should be "laser". Correction is required.

Allowable Subject Matter

- 5. Claims 1-6, 8-17, 19 and 20 are allowed.
- 6. The following is a statement of reasons for the indication of allowable subject matter: The instant application calls for a method of fabricating a polysilicon film by an excimer laser crystallization (ELC) process comprising following steps: providing a substrate, the substrate surface defined with a first region, a second region surrounding the first region, and a third region; forming an amorphous silicon film on the silicon substrate; performing a first photo-etching process to remove parts of the amorphous silicon film in the third region to form an alignment mark in the third region; forming a mask layer on the amorphous silicon film; performing a second photo-etching process to remove the mask layer on the amorphous film in the first region; and performing the excimer laser crystallization process with an excimer laser to make the amorphous film in the first region crystallize to a polysilicon film.

Application/Control Number: 10/604,485

Art Unit: 1756

After a search of the relevant prior art areas, the Examiner has cited the most relevant prior art on the attached PTO-892. However, none of the prior art references show the specific combination of features as claimed. The teachings of Harkin et al. and Lin show the basic features of the instant application except for the designation of a third region on the substrate, and all of the associated processing of the third region to form an alignment mark. The prior art does not contemplate any of these processing steps.

7. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. The Examiner has set forth the reason for indicating allowable subject matter above. The following are the basic teachings of the art cited by the Examiner.

Harkin et al. teaches a method of forming a polysilicon film by an excimer laser crystallization process (Abstract). Harkin et al. shows providing a substrate (having a buffer layer) defined with a first region and a second region (Fig. 1-2, col. 7, lines 1-25,col. 10, lines 1-10). Harkin et al. discloses forming an amorphous silicon film on the substrate, forming a mask layer on the amorphous silicon film, performing a first photoetching process to remove the mask layer on the first region (Fig. 3-5, 13-14, col. 5, lines 50-65 col. 6, lines 1-20, col. 7, lines 24-67, col. 12, lines 49-67, col. 13, lines 1-17).

Harkin et al. teaches forming a heat-retaining capping layer covering the mask layer and the amorphous silicon film (Fig. 3-5, col. 7, lines 40-67). Furthermore, Harkin

Application/Control Number: 10/604,485

Art Unit: 1756

et al. shows performing the excimer laser crystallization process to make the amorphous silicon film in the first region crystallize to a polysilicon film (Fig. 5, col. 6, lines 1-20, col. 8, lines 9-25). Harkin et al. discloses an etching process to remove the heat-retaining layer, the mask layer, and to etch the portions of the amorphous film after forming the polysilicon film (Fig. 13-14, col. 4, lines 24-35, col.9, lines 40-45, col. 13, lines 1-17). Harkin et al. teaches the mask layer and the heat-retaining capping layer comprising silicon oxide, silicon nitride, silicon oxynitride or a metal (col. 3, lines 47-50, 63-67, col. 4, lines 1-4).

Kawasaki et al. teaches the excimer laser having a period from several nanoseconds through several hundred nanoseconds (col. 4, lines 58-67).

Conclusion

8. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Christopher G. Young whose telephone number is 571-272-1394. The examiner can normally be reached on Monday-Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Mark Huff can be reached on 571-272-1385. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Application/Control Number: 10/604,485

Art Unit: 1756

Page 6

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Christopher G. Young

Primary Examiner

Art Unit 1756